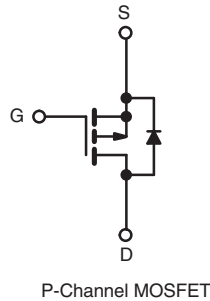


Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 200	
$R_{DS(on)}$ (Ω)	$V_{GS} = -10$ V	3.0
Q_g (Max.) (nC)	13	
Q_{gs} (nC)	3.2	
Q_{gd} (nC)	7.3	
Configuration	Single	

TO-220 FULLPAK


FEATURES

- Isolated Package
- High Voltage Isolation = 2.5 kV_{RMS} (t = 60 s; f = 60 Hz)
- Sink to Lead Creepage Distance = 4.8 mm
- P-Channel
- Dynamic dV/dt Rating
- Low Thermal Resistance
- Lead (Pb)-free Available


RoHS*
COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 FULLPAK eliminates the need for additional insulating hardware in commercial-industrial applications. The moulding compound used provides a high isolation capability and a low thermal resistance between the tab and external heatsink. This isolation is equivalent to using a 100 micron mica barrier with standard TO-220 product. The FULLPAK is mounted to a heatsink using a single clip or by a single screw fixing.

ORDERING INFORMATION

Package	TO-220 FULLPAK
Lead (Pb)-free	IRFI9640GPbF
	SiHFI9640G-E3
SnPb	IRFI9640G
	SiHFI9640G

ABSOLUTE MAXIMUM RATINGS $T_C = 25$ °C, unless otherwise noted

PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	- 200	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25$ °C	- 2.0	A
		$T_C = 100$ °C	- 1.3	
Pulsed Drain Current ^a	I_{DM}	- 8.0		
Linear Derating Factor		0.22	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	100	mJ	
Repetitive Avalanche Current ^a	I_{AR}	- 2.0	A	
Repetitive Avalanche Energy ^a	E_{AR}	2.7	mJ	
Maximum Power Dissipation	P_D	27	W	
Peak Diode Recovery dV/dt ^c	dV/dt	- 11	V/ns	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C	
Soldering Recommendations (Peak Temperature)	for 10 s	300 ^d		
Mounting Torque	6-32 or M3 screw	10	lbf · in	
		1.1	N · m	

Notes



- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting $T_J = 25$ °C, L = 51 mH, $R_G = 25$ Ω , $I_{AS} = -2.0$ A (see fig. 12).
- $I_{SD} \leq -2.0$ A, $dI/dt \leq -250$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 150$ °C.
- 1.6 mm from case.

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	65	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	4.6	

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = -1\text{ mA}$	-	-0.22	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-2.0	-	-4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -200\text{ V}, V_{GS} = 0\text{ V}$	-	-	-100	μA
		$V_{DS} = -160\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	-500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$ $I_D = -1.2\text{ A}^b$	-	-	3.0	Ω
Forward Transconductance	g_{fs}	$V_{DS} = -50\text{ V}, I_D = -1.2\text{ A}^b$	0.7	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = -25\text{ V},$ $f = 1.0\text{ MHz}$, see fig. 5	-	180	-	pF
Output Capacitance	C_{oss}		-	66	-	
Reverse Transfer Capacitance	C_{riss}		-	12	-	
Total Gate Charge	Q_g	$V_{GS} = -10\text{ V}$ $I_D = -2.0\text{ A}, V_{DS} = -160\text{ V},$ see fig. 6 and 13 ^b	-	-	13	nC
Gate-Source Charge	Q_{gs}		-	-	3.2	
Gate-Drain Charge	Q_{gd}		-	-	7.3	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -100\text{ V}, I_D = -2.0\text{ A},$ $R_G = 24\text{ }\Omega, V_{GS} = -10\text{ V},$ see fig. 10 ^b	-	12	-	ns
Rise Time	t_r		-	17	-	
Turn-Off Delay Time	$t_{d(off)}$		-	19	-	
Fall Time	t_f		-	15	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	-2.0	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	-8.0	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = -2.0\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	-5.8	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = -2.0\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	130	200	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	700	1050	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

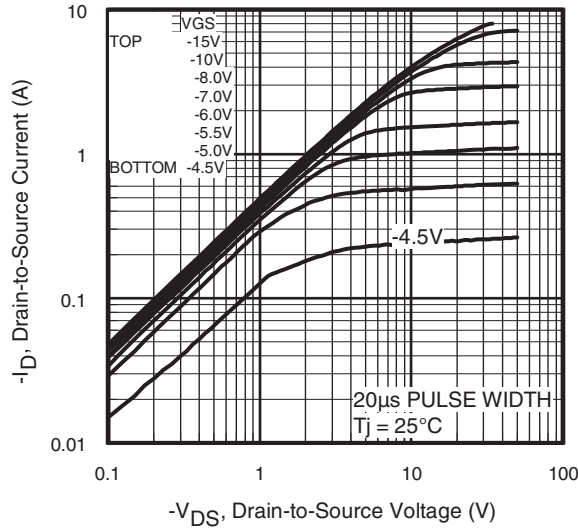


Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

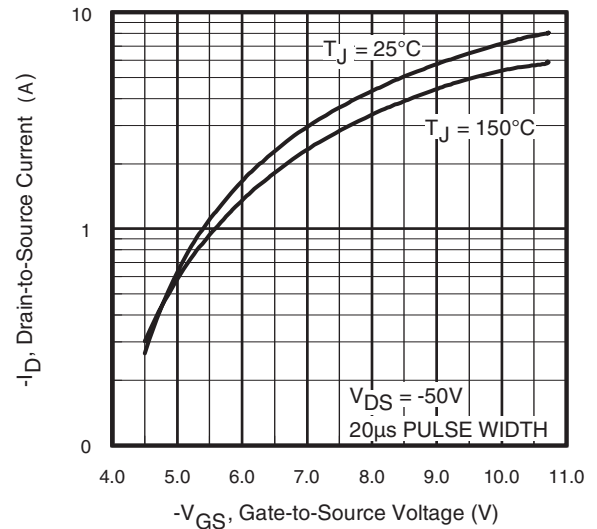


Fig. 3 - Typical Transfer Characteristics

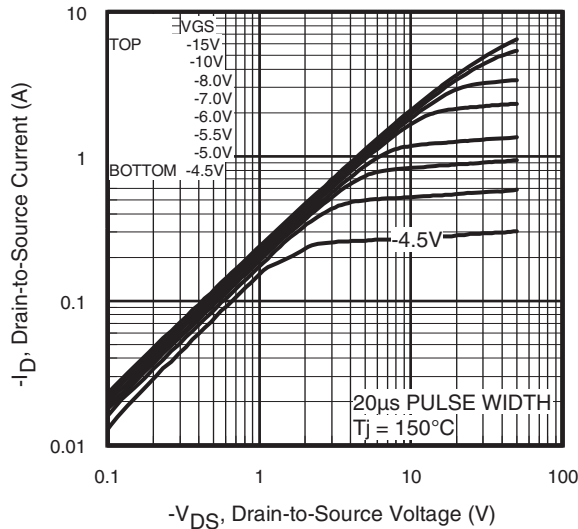


Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

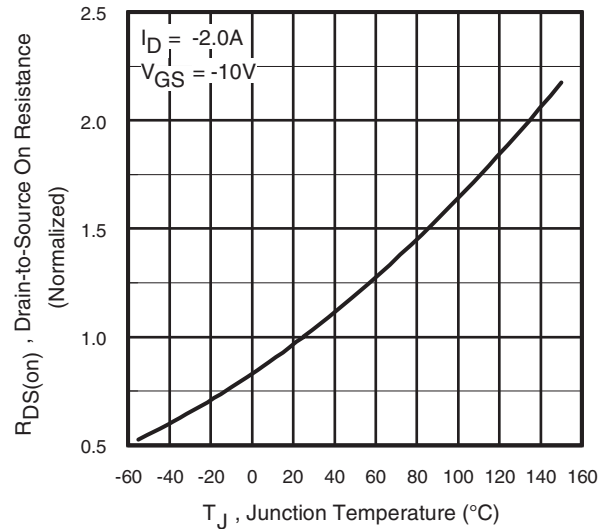


Fig. 4 - Normalized On-Resistance vs. Temperature

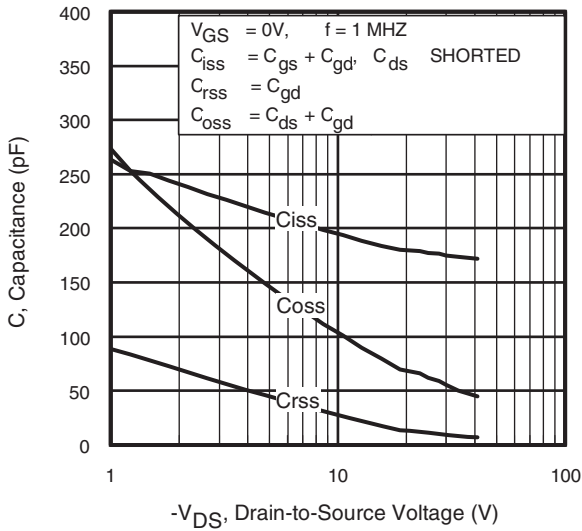


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

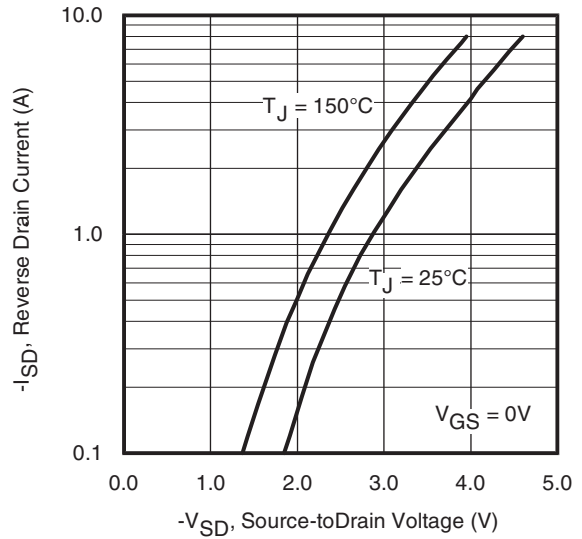


Fig. 7 - Typical Source-Drain Diode Forward Voltage

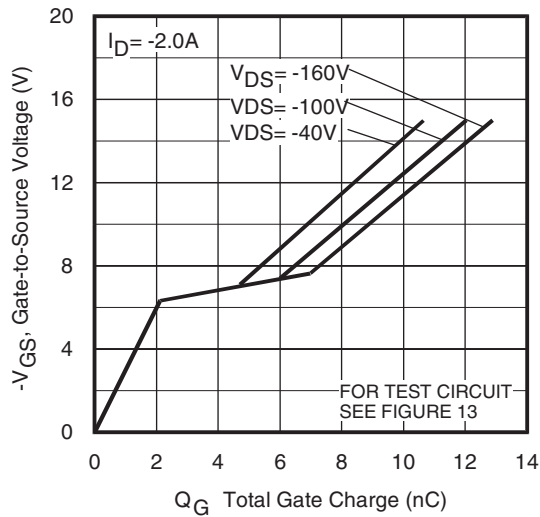


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

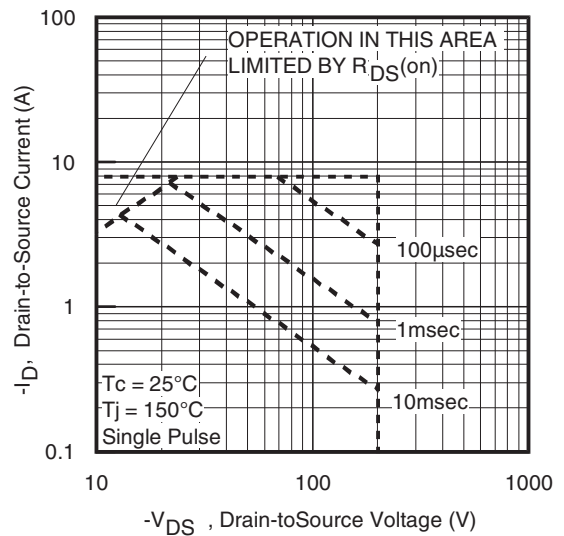


Fig. 8 - Maximum Safe Operating Area

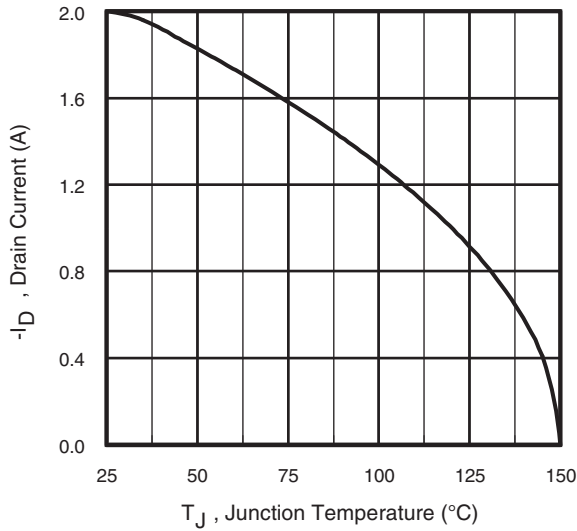


Fig. 9 - Maximum Drain Current vs. Case Temperature

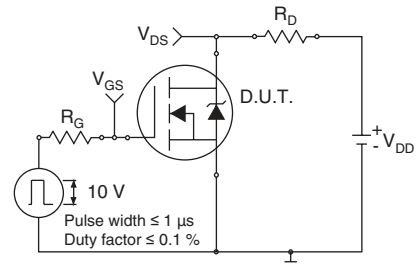


Fig. 10a - Switching Time Test Circuit

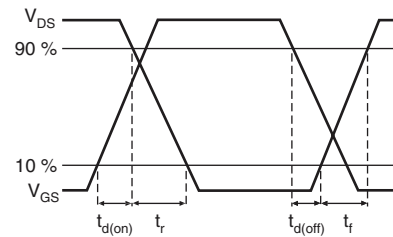


Fig. 10b - Switching Time Waveforms

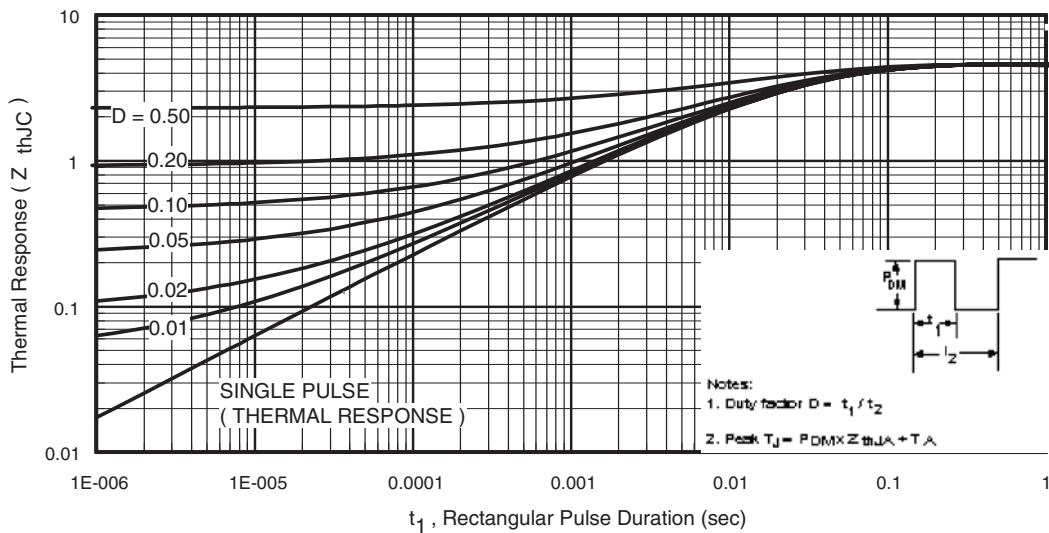


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

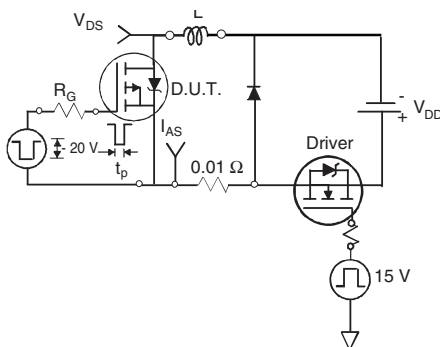


Fig. 12a - Unclamped Inductive Test Circuit

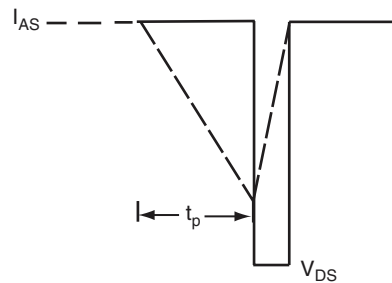


Fig. 12b - Unclamped Inductive Waveforms

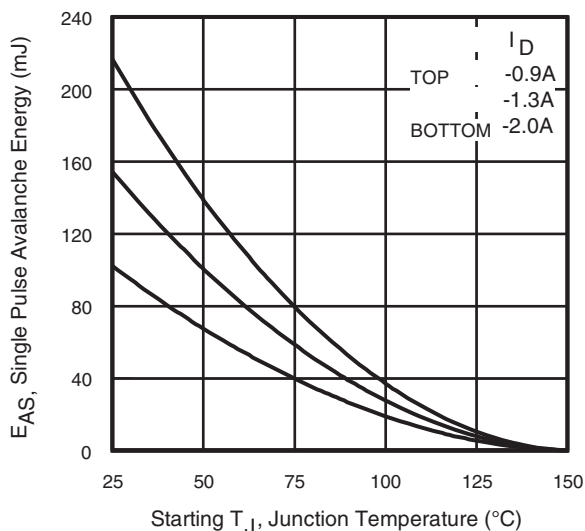


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform

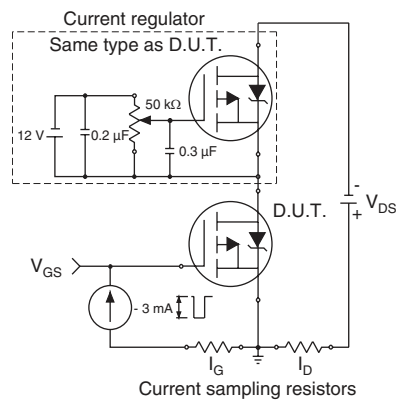
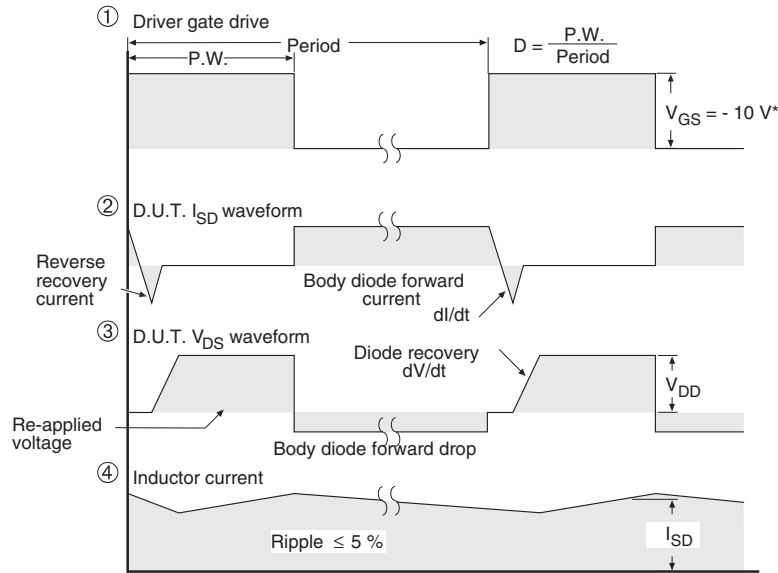
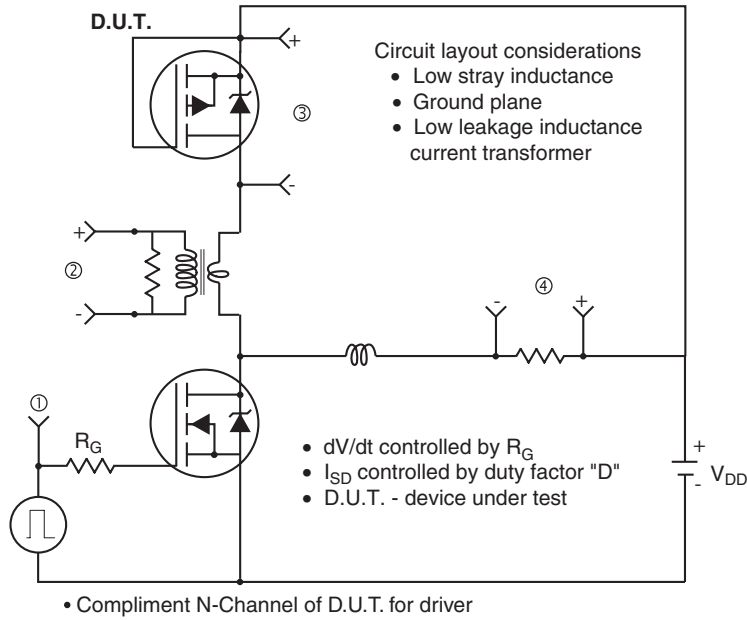


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5V$ for logic level and $-3V$ drive devices

Fig. 14 - For P-Channel

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